

GENERAL PURPOSE AMPLIFIER

RF2043

Typical Applications

- Broadband, Low Noise Gain Blocks
- IF or RF Buffer Amplifiers
- Driver Stage for Power Amplifiers
- Final PA for Low Power Applications
- High Reliability Applications
- Broadband Test Equipment

Product Description

The RF2043 is a general purpose, low cost RF amplifier IC. The device is manufactured on an advanced Gallium Arsenide Heterojunction Bipolar Transistor (HBT) process, and has been designed for use as an easily-cascadable 50Ω gain block. Applications include IF and RF amplification in wireless voice and data communication products operating in frequency bands up to 6000MHz. The device is self-contained with 50Ω input and output impedances and requires only two external DC biasing elements to operate as specified. With a goal of enhanced reliability, the extremely small Micro-X ceramic package offers significantly lower thermal resistance than similar size plastic packages.



Si BJT	🗹 GaAs HBT	GaAs MESFET
Si Bi-CMOS	SiGe HBT	Si CMOS



Functional Block Diagram



NOTES: 1. Shaded lead is pin 1. 2. Darkened areas are metallization.

Package Style: Micro-X Ceramic

Features

- DC to >6000 MHz Operation
- Internally matched Input and Output
- 11 dB Small Signal Gain
- +35dBm Output IP3
- +18.5dBm Output Power
- Extremely Flat Gain Response

Ordering Information RF2043 General Purpose Amplifier RF204X PCBA Fully Assembled Evaluation Board RF Micro Devices, Inc. RF Micro Devices, Inc. RF Micro Devices, Inc. Tel (336) 664 1233 7625 Thorndike Road Greensboro, NC 27409, USA

Rev A4 010110

Absolute Maximum Ratings

Parameter	Rating	Unit		
Supply Current	120	mA		
Input RF Power	+20	dBm		
Operating Ambient Temperature	-40 to +85	°C		
Storage Temperature	-60 to +150	°C		



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Deremeter	Specification		Unit	Condition		
Parameter	Min.	Тур.	Max.	Unit	Condition	
Overall					T=25 °C, V _D =5.5 V, I _{CC} =70mA	
Frequency Range		DC to >6000		MHz		
1 dB Bandwidth		5.5		GHz		
Gain		11.3		dB	Freq=100MHz	
		11.3		dB	Freq=1000MHz	
	10.2	11.4		dB	Freq=2000MHz	
		11.5		dB	Freq=3000MHz	
		11.5			Freq=4000MHz	
		9.9			Freq=6000MHz	
Gain Flatness		±0.05		dB	100MHz to 2000MHz	
Noise Figure		7.6		dB	Freq=1000MHz	
Input VSWR		<1.8:1			In a 50 Ω system, DC to 3000MHz	
		<2.5:1			In a 50 Ω system, 3000MHz to 6000MHz	
Output VSWR		<1.8:1			In a 50 Ω system, DC to 3000MHz	
		<2.6:1			In a 50 Ω system, 3000MHz to 6000MHz	
Output IP ₃		+34.5		dBm	Freq=1000MHz	
Output P _{1dB}		+18.5		dBm	Freq=1000MHz	
Reverse Isolation		16.5		dB	Freq=1000MHz	
Thermal					I _{CC} =70mA, P _{DISS} =370mW	
Theta _{JC}		149		°C/W		
Maximum Measured Junction Temperature at DC Bias Con- ditions		142		°C	T _{AMB} =+85°C	
Mean Time Between Failures		1.4x10 ³		years	T _{AMB} =+85°C	
		3.4x10 ⁵		years	T _{AMB} =+25°C	
		1.8x10 ⁹		years	$T_{AMB} = -40 ^{\circ}\text{C}$	
Power Supply					With 22Ω bias resistor	
Device Operating Voltage	5.0	5.5	6.0	V	At pin 3 with I _{CC} =70mA	
Operating Current		70		mA		

Pin	Function	Description	Interface Schematic
1	RF IN	RF input pin. This pin is NOT internally DC blocked. A DC blocking capacitor, suitable for the frequency of operation, should be used in most applications. DC coupling of the input is not allowed, because this will override the internal feedback loop and cause temperature instability.	
2	GND	Ground connection. Keep traces physically short and connect immedi- ately to ground plane for best performance.	
3	RF OUT	RF output and bias pin. Biasing is accomplished with an external series resistor and choke inductor to V _{CC} . The resistor is selected to set the DC current into this pin to a desired level. The resistor value is determined by the following equation: $R = \frac{(V_{SUPPLY} - V_{DEVICE})}{I_{CC}}$ Care should also be taken in the resistor selection to ensure that the current into the part never exceeds 120 mA over the planned operating temperature . This means that a resistor between the supply and this pin is always required, even if a supply near 5.5V is available, to provide DC feedback to prevent thermal runaway. Because DC is present on this pin, a DC blocking capacitor, suitable for the frequency of operation, should be used in most applications. The supply side of the bias network should also be well bypassed.	RF INO
4	GND	Same as pin 2.	

Application Schematic



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Evaluation Board Layout Board Size 1.195" x 1.000"





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Noise Figure versus Frequency Across Temperature



Output VSWR versus Frequency Across Temperature



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 $H_{CC} = 70 \text{ mA}$

Reverse Isolation versus Frequency Across Temperature